# Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

| PRODUCT SUMMARY | | | | |
|---|---|---|---|---|
| | $V_{DS}$ (V) | $r_{DS(on)}$ (Ω) | $I_D$ (A) | $Q_g$ (Typ) |
| Channel-1 | 30 | 0.0185 at $V_{GS}$ = 10 V | 6.8 | 7.8 |
| | | 0.0225 at $V_{GS}$ = 4.5 V | 6.0 | |
| Channel-2 | | 0.0115 at $V_{GS}$ = 10 V | 11.4 | 11.6 |
| | | 0.016 at $V_{GS}$ = 4.5 V | 9.5 | |

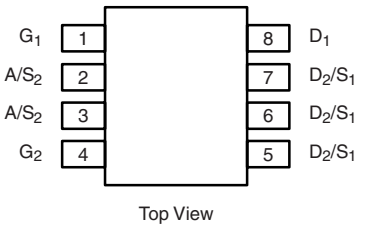
| SCHOTTKY PRODUCT SUMMARY | | |
|---|---|---|
| $V_{DS}$ (V) | $V_{SD}$ (V) Diode Forward Voltage | $I_F$ (A) |
| 30 | 0.50 V at 1.0 A | 2.0 |

## FEATURES

- LITTLE FOOT® *Plus* Power MOSFET
- 100 % $R_g$ Tested

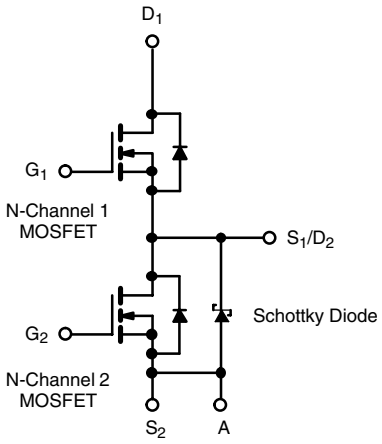
Pb-free
RoHS COMPLIANT

SO-8




Top View

**Ordering Information:** Si4816BDY-T1-E3 (Lead (Pb)-free)




| ABSOLUTE MAXIMUM RATINGS $T_A$ = 25 °C, unless otherwise noted | | | | | | | |
|---|---|---|---|---|---|---|---|
| Parameter | | Symbol | Channel-1 | | Channel-2 | | Unit |
| | | | 10 sec | Steady State | 10 sec | Steady State | |
| Drain-Source Voltage | | $V_{DS}$ | 30 | | | | V |
| Gate-Source Voltage | | $V_{GS}$ | 20 | | | | |
| Continuous Drain Current ($T_J$ = 150 °C)[a] | $T_A$ = 25 °C | $I_D$ | 6.8 | 5.8 | 11.4 | 8.2 | A |
| | $T_A$ = 70 °C | | 5.5 | 4.6 | 9.0 | 6.5 | |
| Pulsed Drain Current | | $I_{DM}$ | 30 | | 40 | | |
| Continuous Source Current (Diode Conduction)[a] | | $I_S$ | 1 | 0.9 | 2.2 | 1.15 | |
| Single Pulse Avalanche Current | L = 0.1 mH | $I_{AS}$ | 10 | | 20 | | |
| Avalanche Energy | | $E_{AS}$ | 5 | | 20 | | mJ |
| Maximum Power Dissipation[a] | $T_A$ = 25 °C | $P_D$ | 1.4 | 1.0 | 2.4 | 1.25 | W |
| | $T_A$ = 70 °C | | 0.9 | 0.64 | 1.5 | 0.8 | |
| Operating Junction and Storage Temperature Range | | $T_J$, $T_{stg}$ | - 55 to 150 | | | | °C |

| THERMAL RESISTANCE RATINGS | | | | | | | | | |
|---|---|---|---|---|---|---|---|---|---|
| Parameter | | Symbol | Channel-1 | | Channel-2 | | Schottky | | Unit |
| | | | Typ | Max | Typ | Max | Typ | Max | |
| Maximum Junction-to-Ambient[a] | t ≤ 10 sec | $R_{thJA}$ | 72 | 90 | 43 | 53 | 48 | 60 | °C/W |
| | Steady State | | 100 | 125 | 82 | 100 | 80 | 100 | |
| Maximum Junction-to-Foot (Drain) | Steady State | $R_{thJF}$ | 51 | 63 | 25 | 30 | 28 | 35 | |

Notes:
a. Surface Mounted on 1" x 1" FR4 Board.

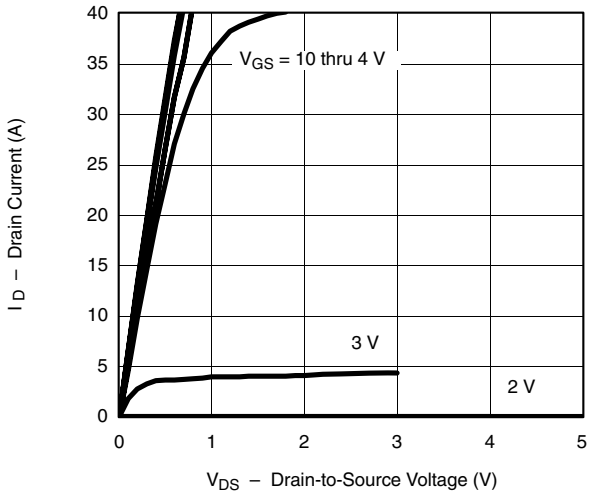
| **MOSFET SPECIFICATIONS** $T_J$ = 25 °C, unless otherwise noted | | | | | | | |
|---|---|---|---|---|---|---|---|
| **Parameter** | **Symbol** | **Test Conditions** | | **Min** | **Typ[a]** | **Max** | **Unit** |
| **Static** | | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D$ = 250 µA | Ch-1 | 1.0 | | 3.0 | V |
| | | | Ch-2 | 1.0 | | 3.0 | |
| Gate-Body Leakage | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = 20 V | Ch-1 | | | 100 | nA |
| | | | Ch-2 | | | 100 | |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = 30 V, $V_{GS}$ = 0 V | Ch-1 | | | 1 | µA |
| | | | Ch-2 | | | 100 | |
| | | $V_{DS}$ = 30 V, $V_{GS}$ = 0 V, $T_J$ = 85 °C | Ch-1 | | | 15 | |
| | | | Ch-2 | | | 2000 | |
| On-State Drain Current[b] | $I_{D(on)}$ | $V_{DS}$ = 5 V, $V_{GS}$ = 10 V | Ch-1 | 20 | | | A |
| | | | Ch-2 | 30 | | | |
| Drain-Source On-State Resistance[b] | $r_{DS(on)}$ | $V_{GS}$ = 10 V, $I_D$ = 6.8 A | Ch-1 | | 0.0155 | 0.0185 | Ω |
| | | $V_{GS}$ = 10 V, $I_D$ = 11.4 A | Ch-2 | | 0.0093 | 0.0115 | |
| | | $V_{GS}$ = 4.5 V, $I_D$ = 6.0 A | Ch-1 | | 0.0185 | 0.0225 | |
| | | $V_{GS}$ = 4.5 V, $I_D$ = 9.5 A | Ch-2 | | 0.013 | 0.016 | |
| Forward Transconductance[b] | $g_{fs}$ | $V_{DS}$ = 15 V, $I_D$ = 6.8 A | Ch-1 | | 30 | | S |
| | | $V_{DS}$ = 15 V, $I_D$ = 11.4 A | Ch-2 | | 31 | | |
| Diode Forward Voltage[b] | $V_{SD}$ | $I_S$ = 1 A, $V_{GS}$ = 0 V | Ch-1 | | 0.73 | 1.1 | V |
| | | $I_S$ = 1 A, $V_{GS}$ = 0 V | Ch-2 | | 0.47 | 0.5 | |
| **Dynamic[a]** | | | | | | | |
| Total Gate Charge | $Q_g$ | Channel-1 $V_{DS}$ = 15 V, $V_{GS}$ = 5 V, $I_D$ = 6.8 A<br>Channel-2 $V_{DS}$ = 15 V, $V_{GS}$ = 5 V, $I_D$ = - 11.4 A | Ch-1 | | 7.8 | 10 | nC |
| | | | Ch-2 | | 11.6 | 18 | |
| Gate-Source Charge | $Q_{gs}$ | | Ch-1 | | 2.9 | | |
| | | | Ch-2 | | 4.8 | | |
| Gate-Drain Charge | $Q_{gd}$ | | Ch-1 | | 2.3 | | |
| | | | Ch-2 | | 3.7 | | |
| Gate Resistance | $R_g$ | | Ch-1 | 1.5 | 3.0 | 4.5 | Ω |
| | | | Ch-2 | 0.9 | 1.8 | 2.7 | |
| Turn-On Delay Time | $t_{d(on)}$ | Channel-1 $V_{DD}$ = 15 V, $R_L$ = 15 Ω $I_D \cong$ 1 A, $V_{GEN}$ = 10 V, $R_g$ = 6 Ω<br>Channel-2 $V_{DD}$ = 15 V, $R_L$ = 15 Ω $I_D \cong$ 1 A, $V_{GEN}$ = 10 V, $R_g$ = 6 Ω | Ch-1 | | 11 | 17 | ns |
| | | | Ch-2 | | 13 | 20 | |
| Rise Time | $t_r$ | | Ch-1 | | 9 | 15 | |
| | | | Ch-2 | | 9 | 15 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | Ch-1 | | 24 | 40 | |
| | | | Ch-2 | | 31 | 50 | |
| Fall Time | $t_f$ | | Ch-1 | | 9 | 15 | |
| | | | Ch-2 | | 11 | 17 | |
| Source-Drain Reverse Recovery Time | $t_{rr}$ | $I_F$ = 1.3 A, di/dt = 100 A/µs | Ch-1 | | 20 | 35 | |
| | | $I_F$ = 2.2 A, di/dt = 100 µA/µs | Ch-2 | | 25 | 40 | |

Notes:
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

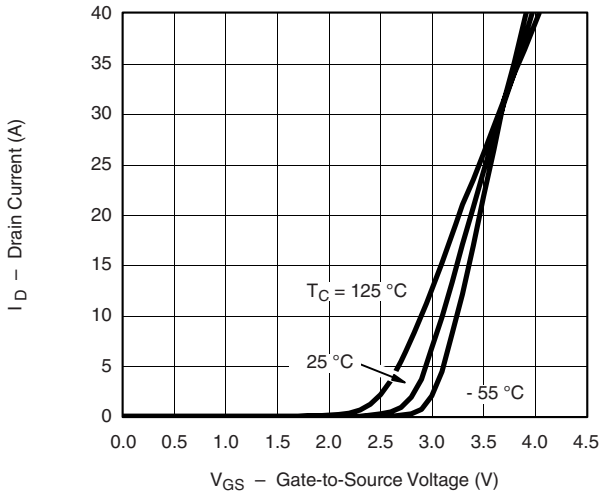
| **SCHOTTKY SPECIFICATIONS** $T_J$ = 25 °C, unless otherwise noted | | | | | | |
|---|---|---|---|---|---|---|
| **Parameter** | **Symbol** | **Test Conditions** | **Min** | **Typ** | **Max** | **Unit** |
| Forward Voltage Drop | $V_F$ | $I_F$ = 1.0 A | | 0.47 | 0.50 | V |
| | | $I_F$ = 1.0 A, $T_J$ = 125 °C | | 0.36 | 0.42 | |
| Maximum Reverse Leakage Current | $I_{rm}$ | $V_r$ = 30 V | | 0.004 | 0.100 | mA |
| | | $V_r$ = 30 V, $T_J$ = 100 °C | | 0.7 | 10 | |
| | | $V_r$ = - 30 V, $T_J$ = 125 °C | | 3.0 | 20 | |
| Junction Capacitance | $C_T$ | $V_r$ = 10 V | | 50 | | pF |

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

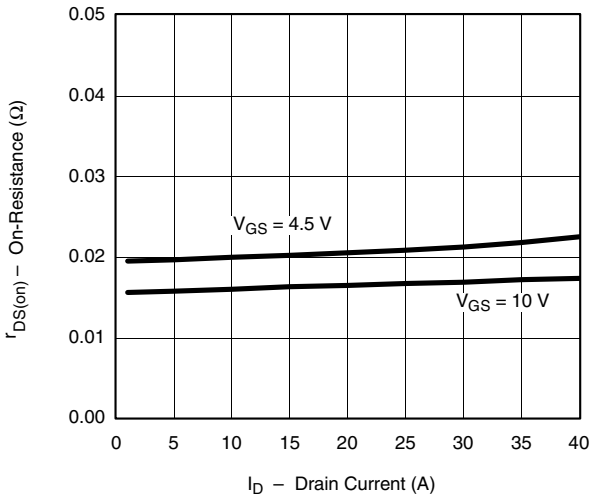
## CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless noted



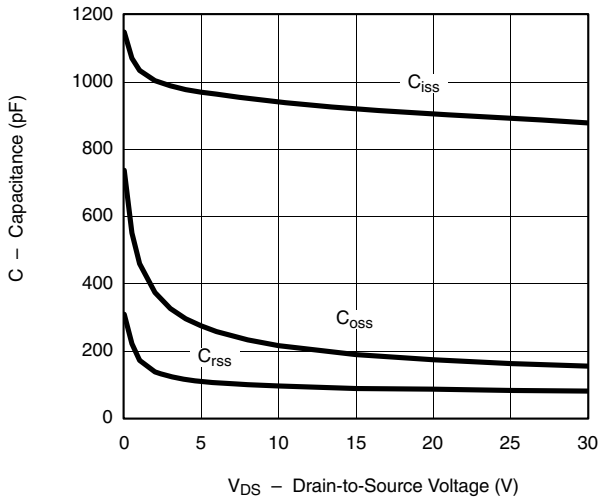

**Output Characteristics**




**Transfer Characteristics**

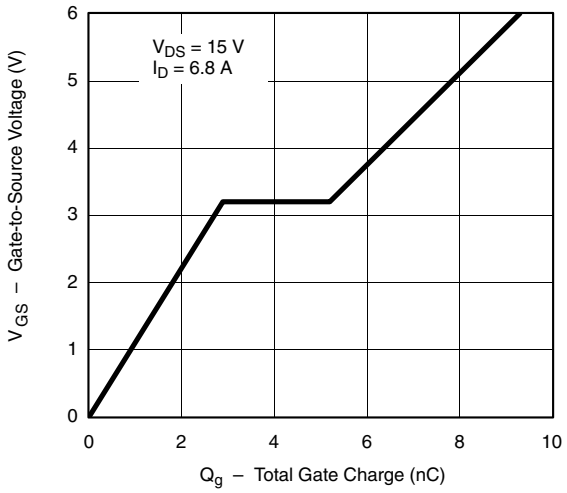



**On-Resistance vs. Drain Current**

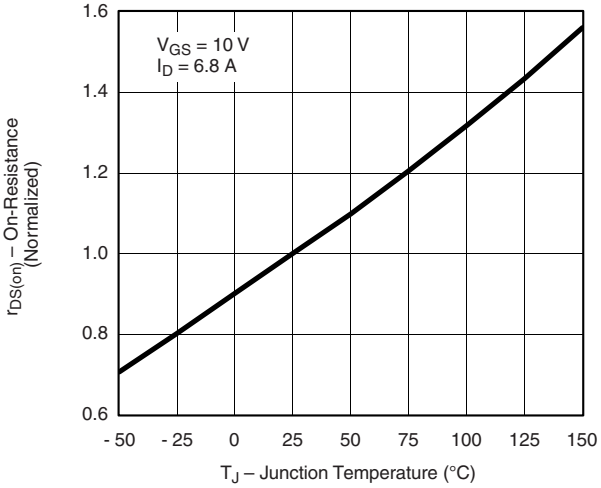



**Capacitance**

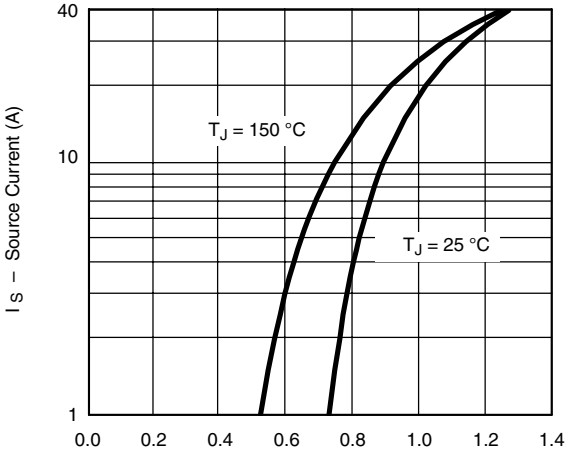
## CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless noted



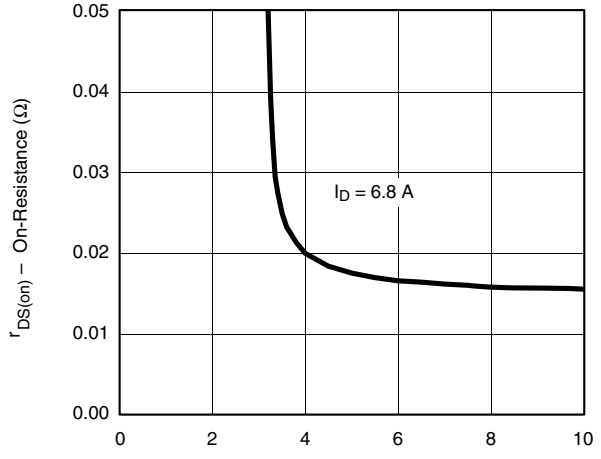

**Gate Charge**



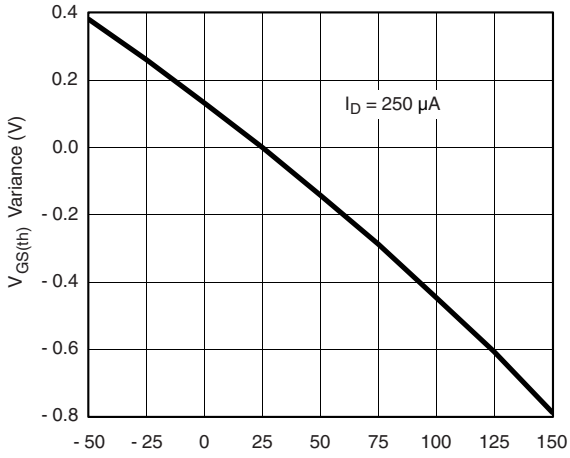

**On-Resistance vs. Junction Temperature**



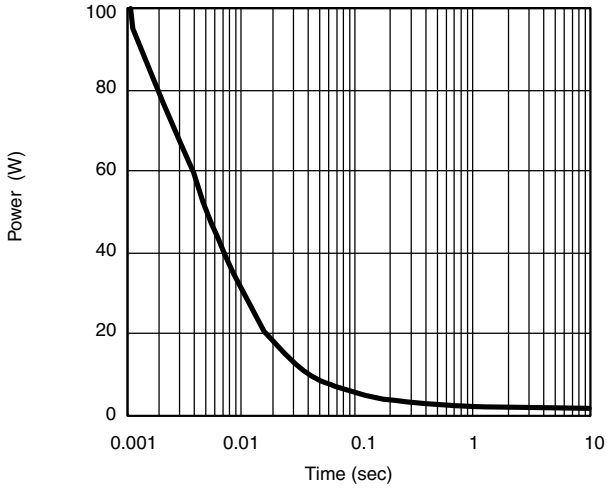

**Source-Drain Diode Forward Voltage**




**On-Resistance vs. Gate-to-Source Voltage**

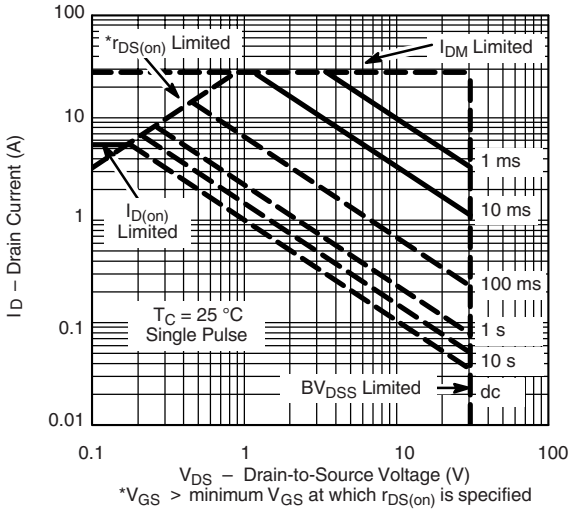



**Threshold Voltage**

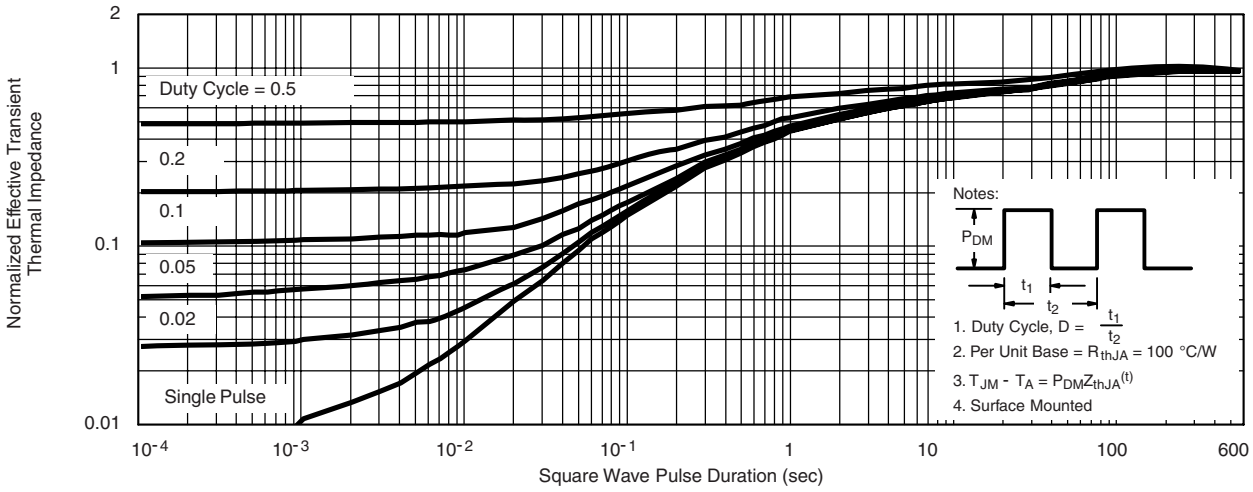



**Single Pulse Power, Junction-to-Ambient**

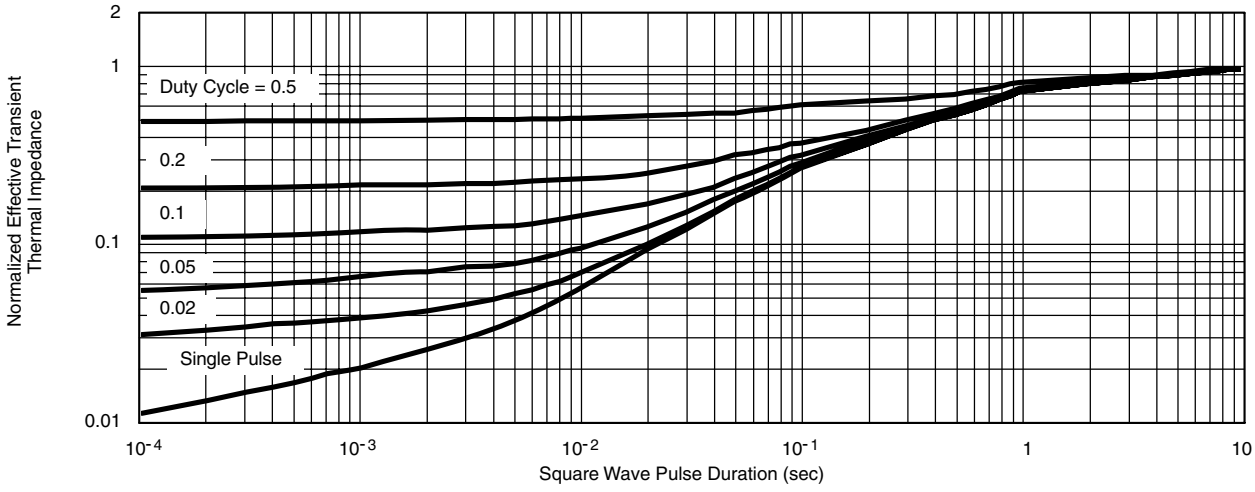
## CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless noted




**Safe Operating Area**

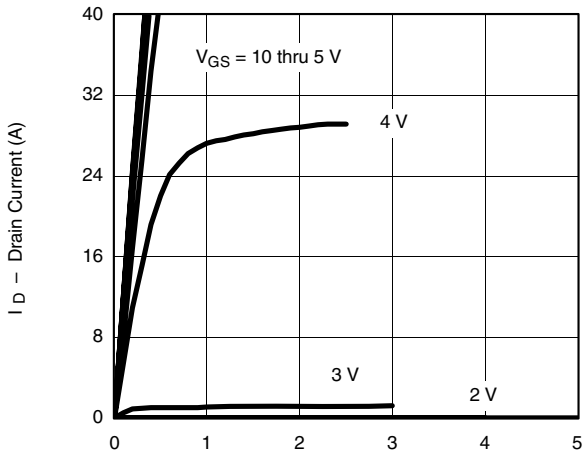



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

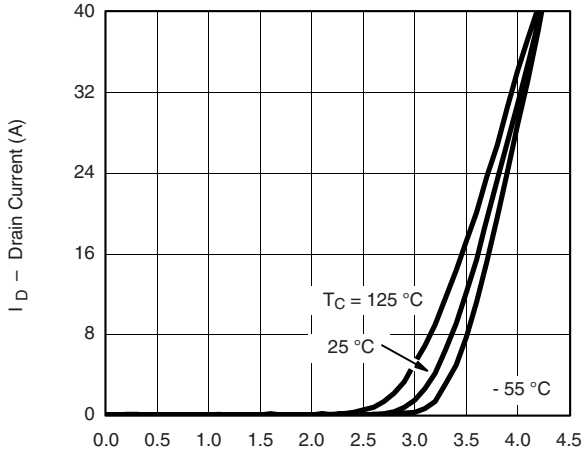



**Normalized Thermal Transient Impedance, Junction-to-Foot**

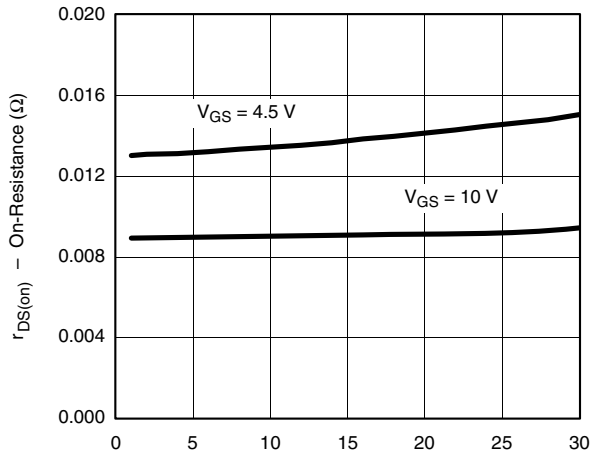
## CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless noted



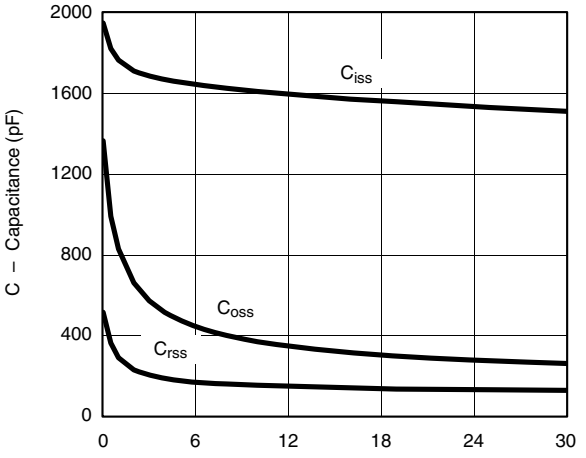

**Output Characteristics**



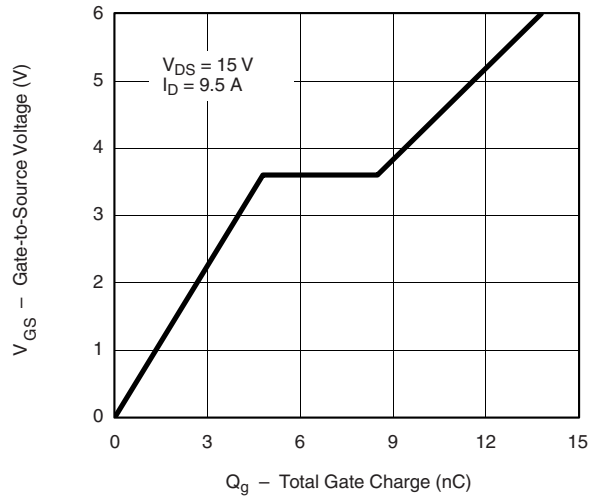

**Transfer Characteristics**



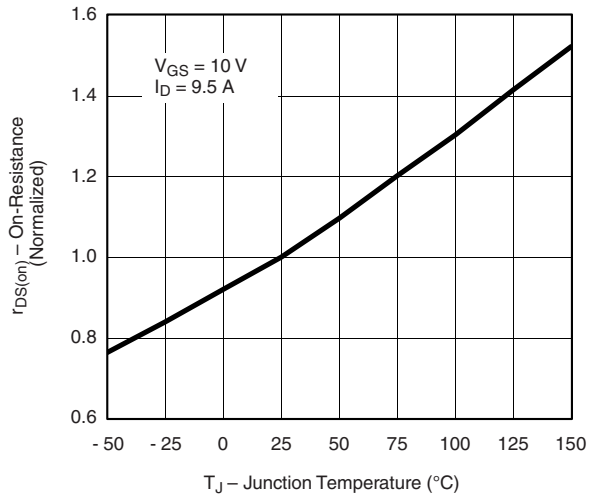

**On-Resistance vs. Drain Current**




**Capacitance**

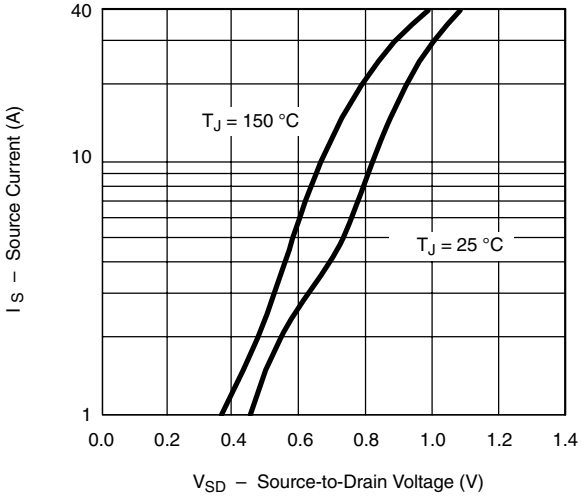



**Gate Charge**

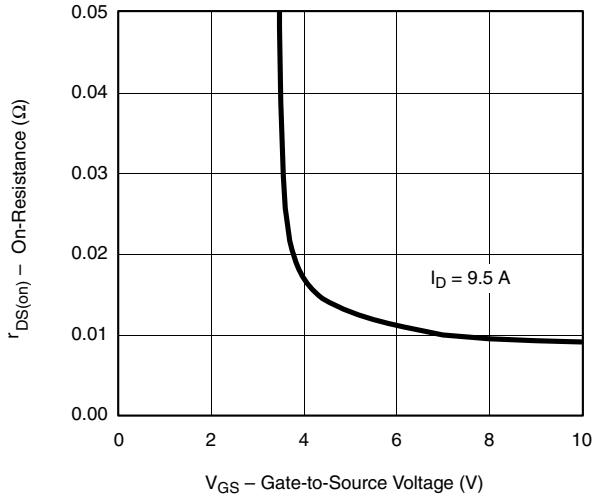



**On-Resistance vs. Junction Temperature**

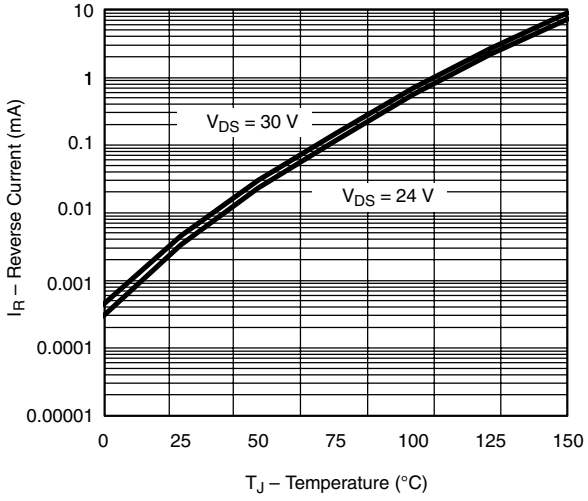
## CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless noted



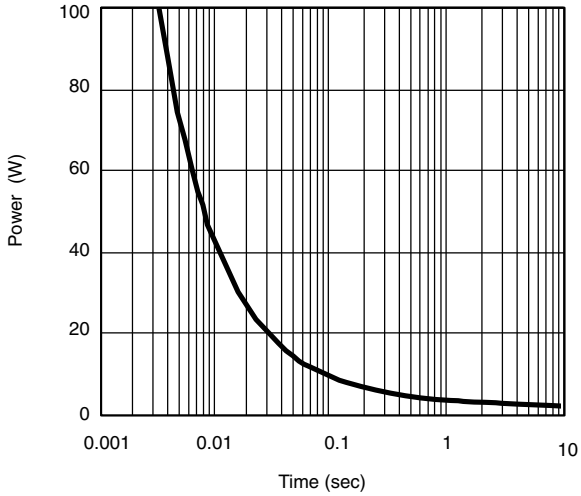

**Source-Drain Diode Forward Voltage**



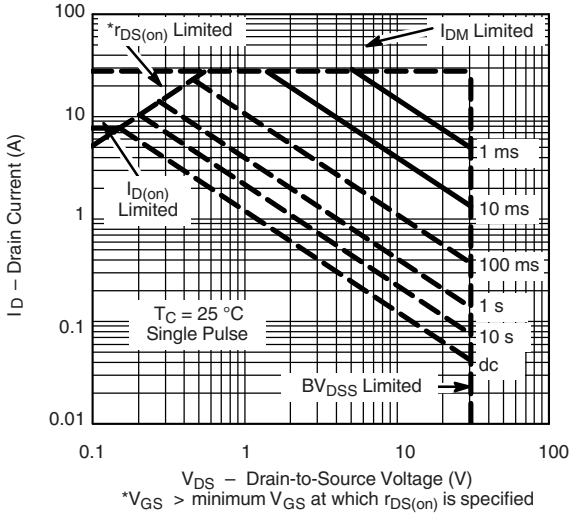

**On-Resistance vs. Gate-to-Source Voltage**




**Reverse Current vs. Junction Temperature**

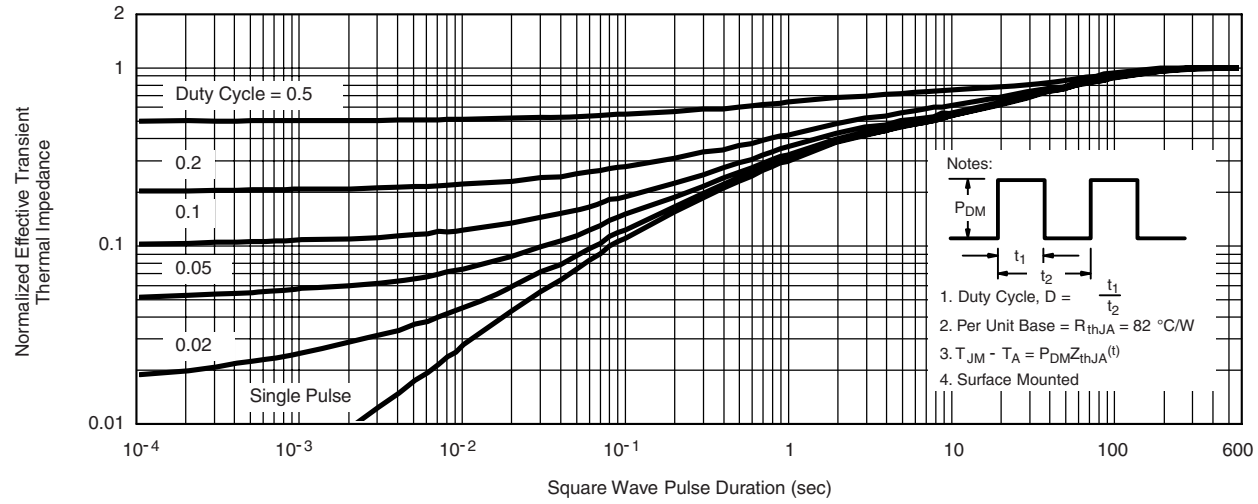



**Single Pulse Power, Junction-to-Ambient**

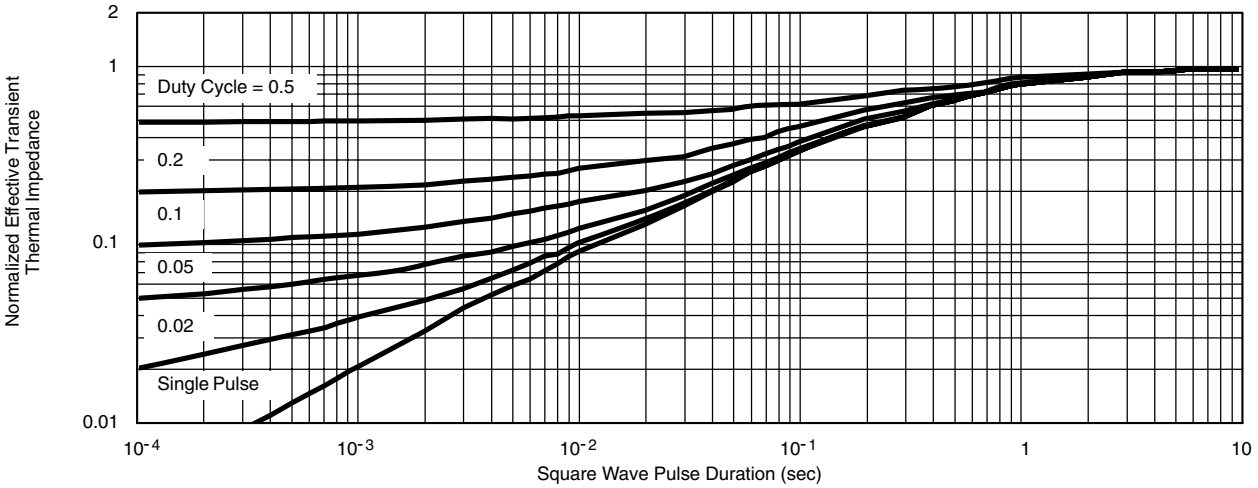



**Safe Operating Area**

## CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless noted

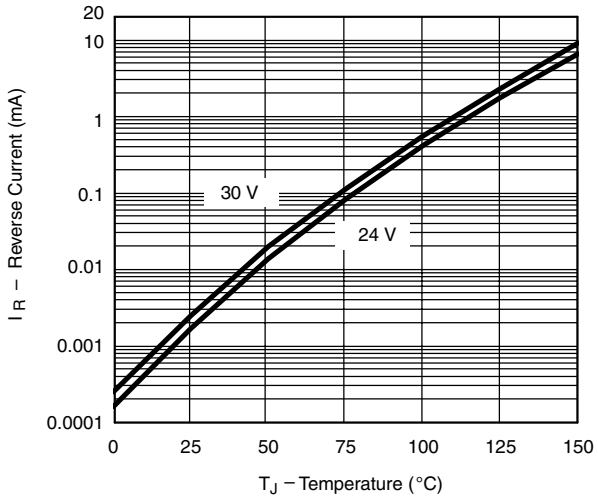



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

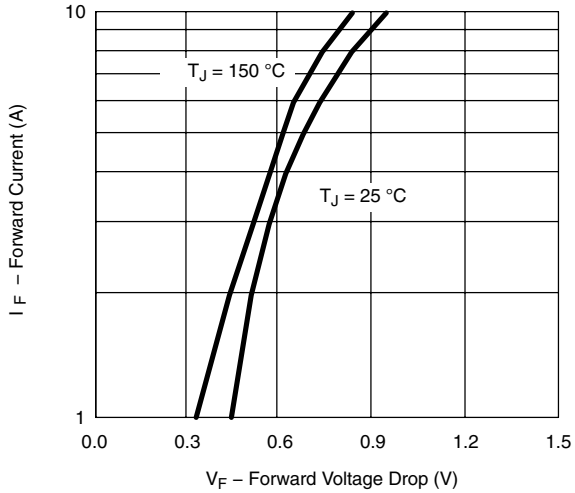



**Normalized Thermal Transient Impedance, Junction-to-Foot**

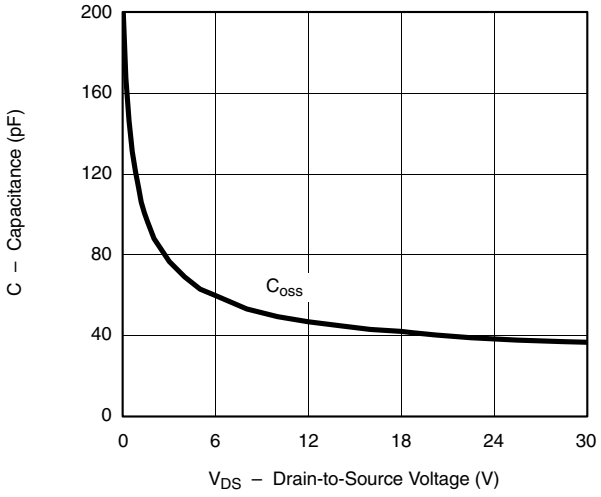
## SCHOTTKY TYPICAL CHARACTERISTICS 25 °C, unless noted




**Reverse Current vs. Junction Temperature**




**Forward Voltage Drop**




**Capacitance**

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